



JMP(C.E.F)10N65B

Description

JMP N-channel MOSFET

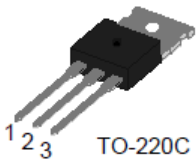
Features

- 650V, 10A
- $R_{DS(ON)} = 0.85\Omega$ (Typ.) @ $V_{GS} = 10V, I_D = 5A$
- Fast Switching
- Improved dv/dt Capability
- 100% Avalanche Tested

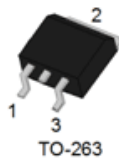
Application

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply(UPS)
- Power Factor Correction (PFC)

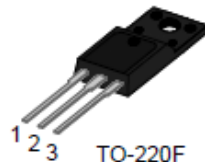
Package



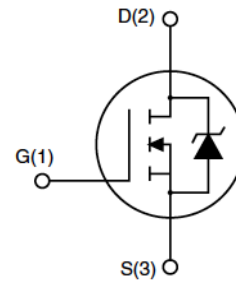
JMPC10N65B



JMPE10N65B



JMPF10N65B



Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Max.		Units	
		TO-220F	TO-220C/TO-263		
V _{DSS}	Drain-Source Voltage	650		V	
V _{GSS}	Gate-Source Voltage	±30		V	
I _D	Continuous Drain Current	T _C = 25°C	10	A	
		T _C = 100°C	6.5	A	
I _{DM}	Pulsed Drain Current ^{note1}	40		A	
E _{AS}	Single Pulsed Avalanche Energy ^{note2}	80		mJ	
P _D	Power Dissipation	T _C = 25°C	64	160	W
R _{θJC}	Thermal Resistance, Junction to Case	1.95	0.78	°C/W	
R _{θJA}	Thermal Resistance, Junction to Ambient	62.5	62.5	°C/W	
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150		°C	



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Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	650	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=650V, V_{GS}=0V, T_J=25^\circ\text{C}$	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 30V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
$R_{DS(on)}$ <small>note3</small>	Static Drain-Source on-Resistance	$V_{GS}=10V, I_D=5A$	-	0.85	1.0	Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1.0\text{MHz}$	-	1110	-	pF
C_{oss}	Output Capacitance		-	129	-	pF
C_{riss}	Reverse Transfer Capacitance		-	20	-	pF
Q_g	Total Gate Charge	$V_{DD}=520V, I_D=10A, V_{GS}=10V$	-	32	-	nC
Q_{gs}	Gate-Source Charge		-	5	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	16	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=325V, I_D=10A, R_G=25\Omega$	-	23	-	ns
t_r	Turn-on Rise Time		-	15	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	90	-	ns
t_f	Turn-off Fall Time		-	30	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	10	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	40	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_{SD}=10A$	-	-	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS}=0V, I_S=10A, di/dt=100A/\mu s$	-	310	-	ns
Q_{rr}	Reverse Recovery Charge		-	4.1	-	μC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. $I_{AS}=6A, V_{DD}=50V, R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$

3. Pulse Test: Pulse Width $\leq 325\mu s$, Duty Cycle $\leq 1\%$



Typical Performance Characteristics

Figure 1: Output Characteristics

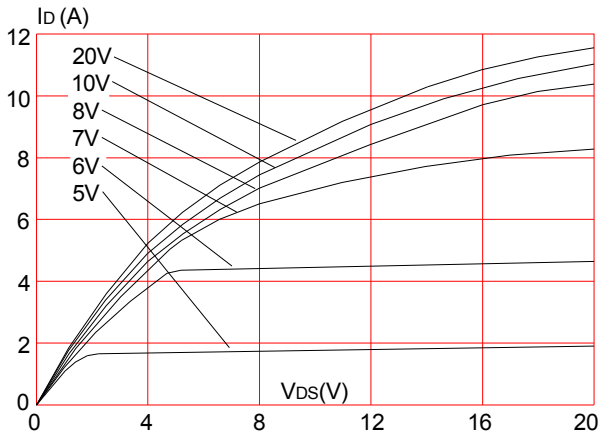


Figure 2: Typical Transfer Characteristics

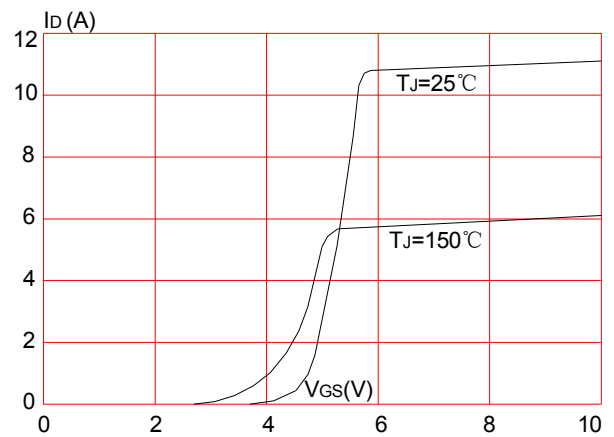


Figure 3: On-resistance vs. Drain Current

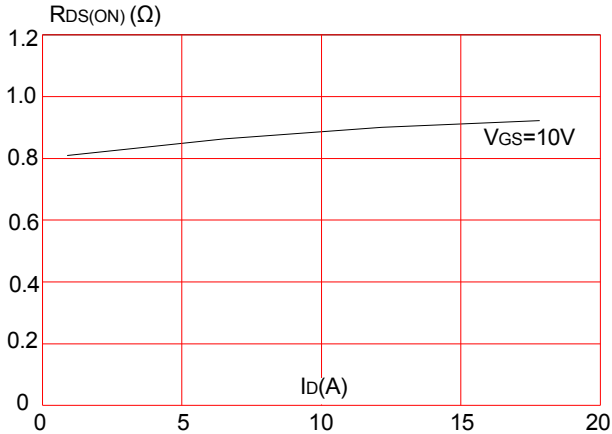


Figure 4: Body Diode Characteristics

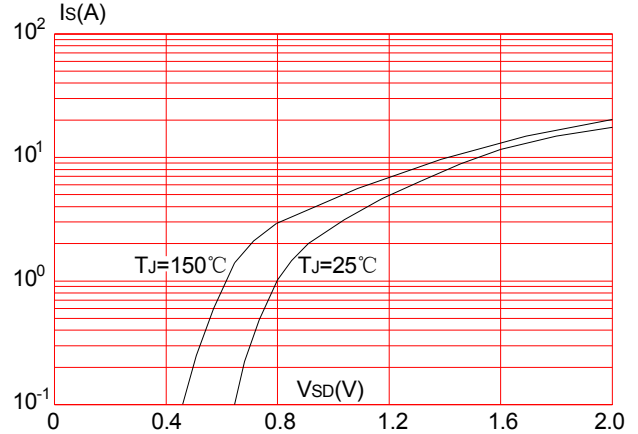


Figure 5: Gate Charge Characteristics

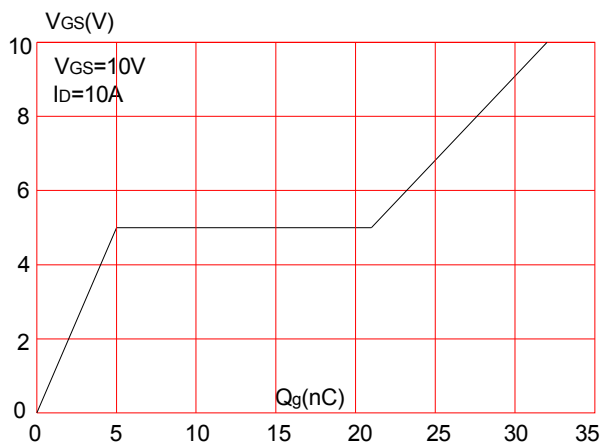
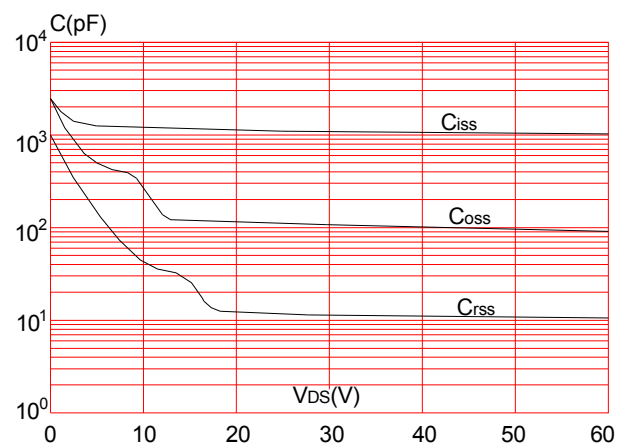


Figure 6: Capacitance Characteristics





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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

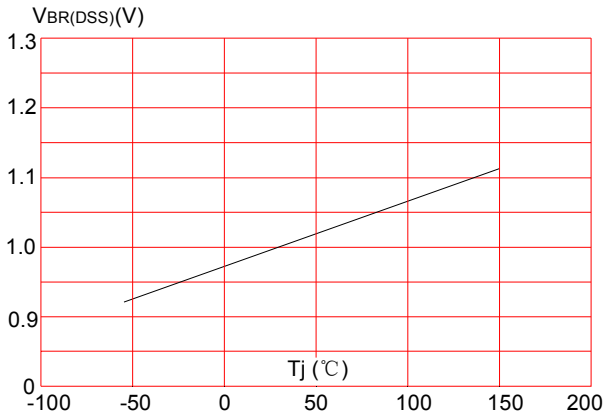


Figure 8: Normalized on Resistance vs. Junction Temperature

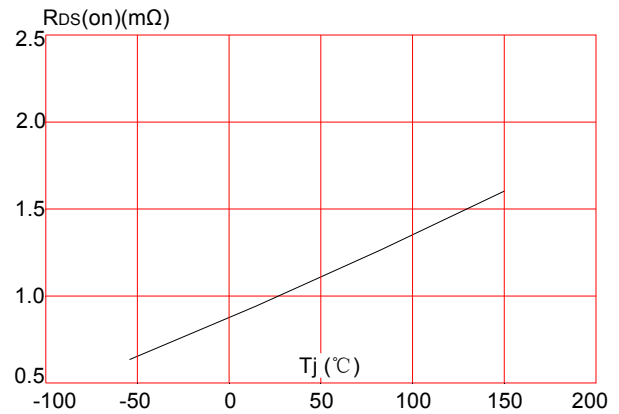


Figure 9: Maximum Safe Operating Area

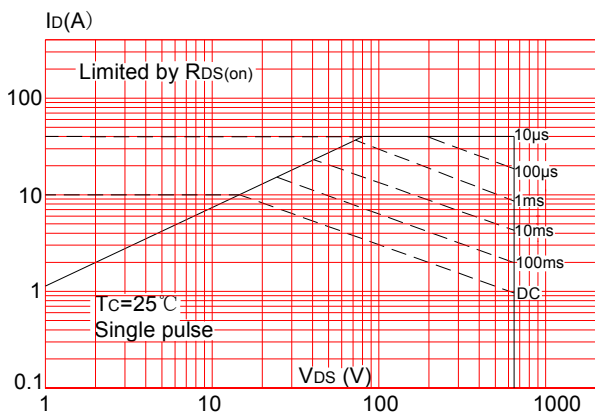


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

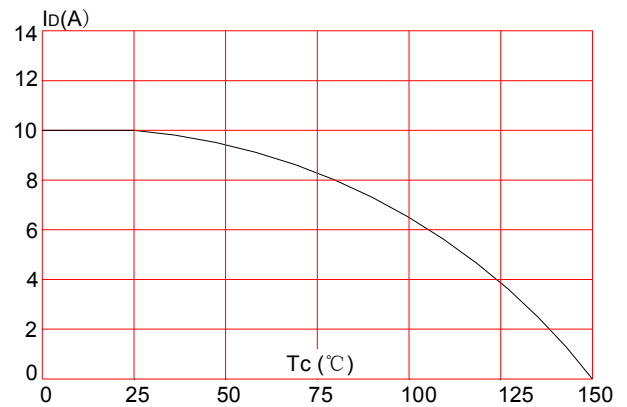


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220F)

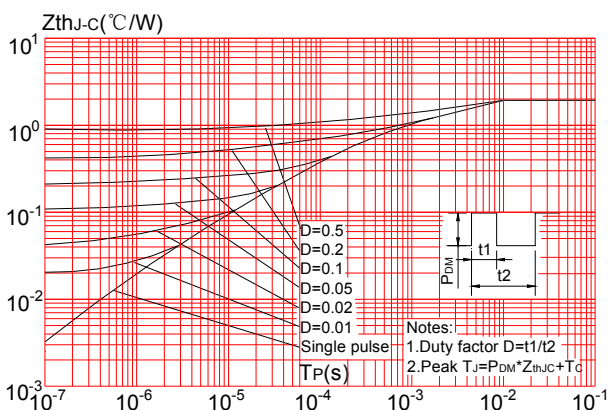
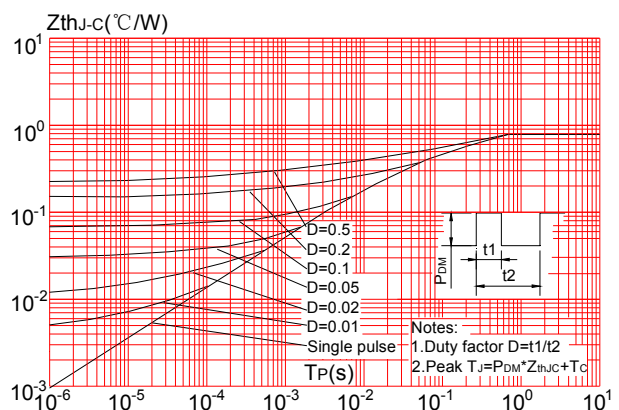


Figure.12: Maximum Effective Transient Thermal Impedance, Junction-to-Case (TO-220C, TO-263)



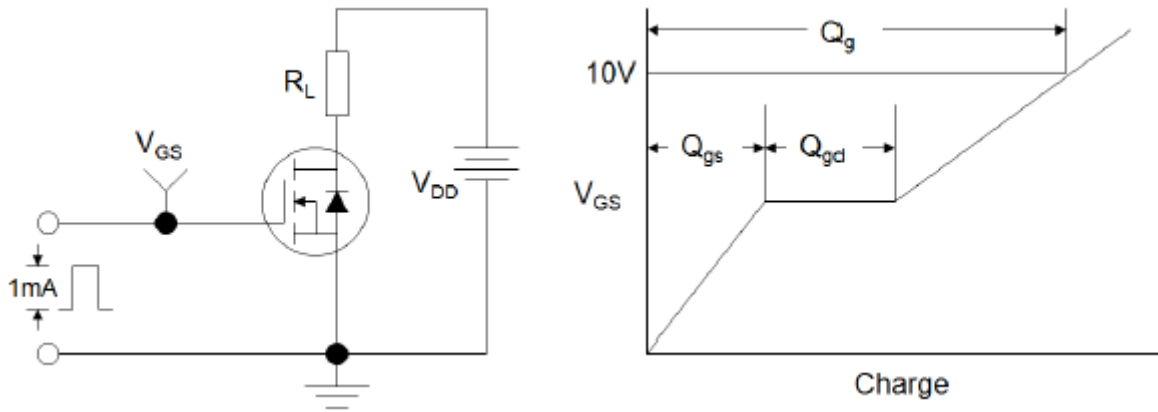


Figure 1: Gate Charge Test Circuit & Waveform

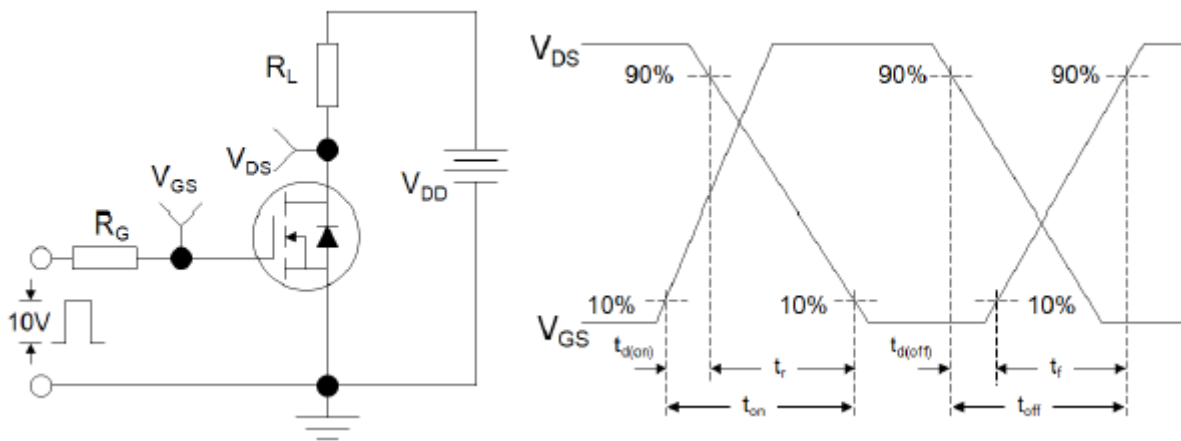


Figure 2: Resistive Switching Test Circuit & Waveforms

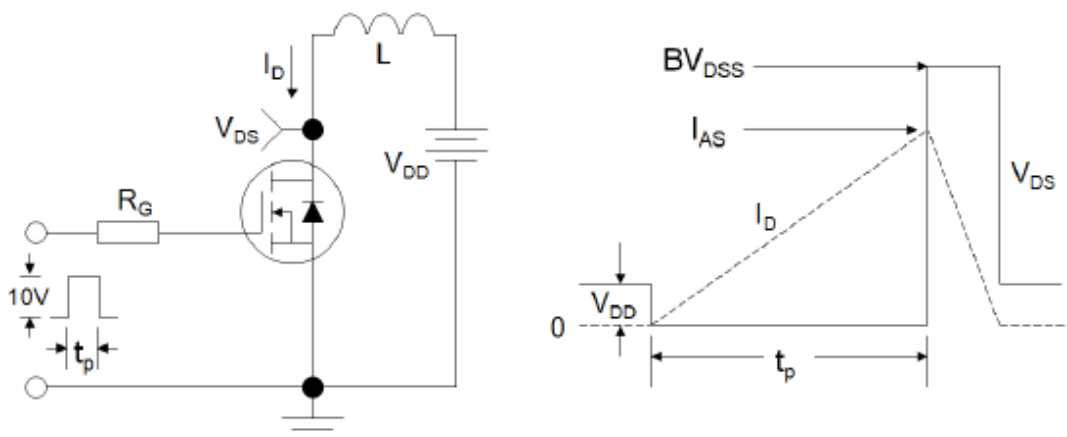


Figure 3: Unclamped Inductive Switching Test Circuit & Waveforms

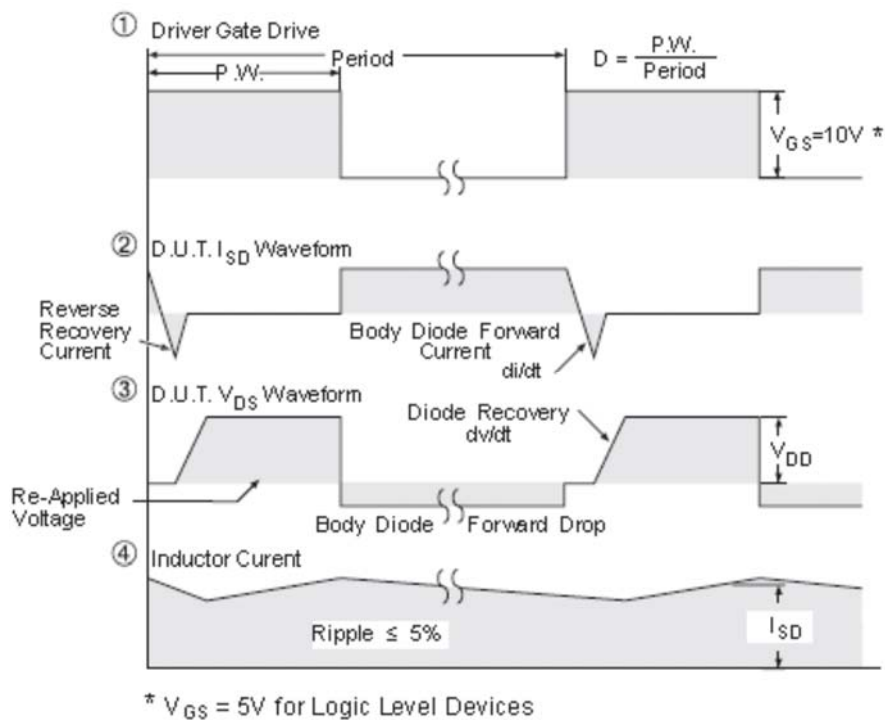
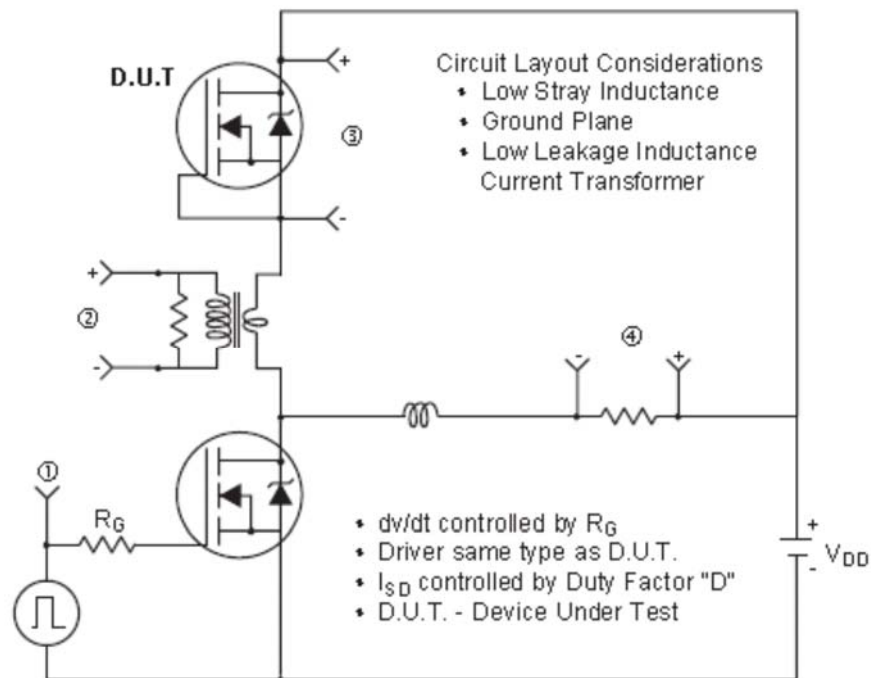
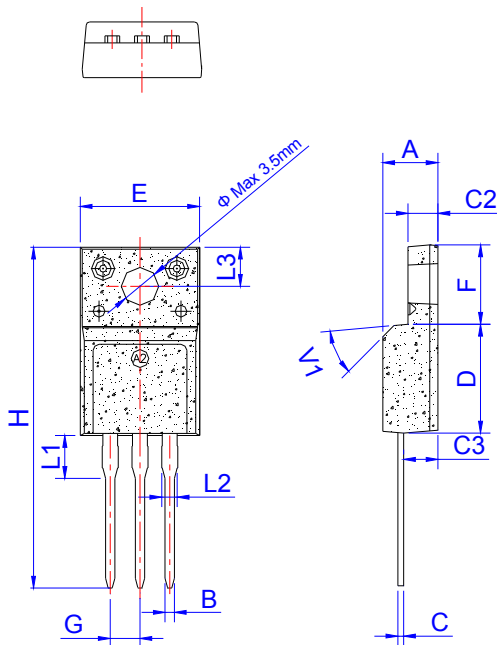


Figure 4: Peak Diode Recovery dv/dt Test Circuit & Waveforms (For N-channel)



Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

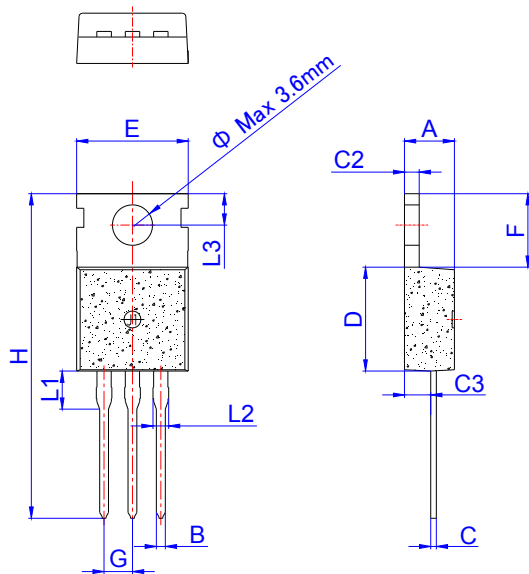
Package Information -TO-220F

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	50	1,000	8,000



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Package Mechanical Data



TO-220C

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
Φ		3.6			0.142	

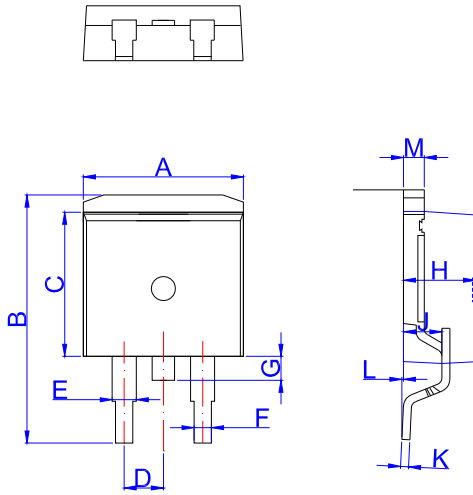
Package Information -TO-220C

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	50	1,000	8,000



JMP(C.E.F)10N65B

Package Mechanical Data



TO-263

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.4		9.6	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053

Package Information -TO-263

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	50	1,000	8,000

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